
Subject: Energy loss in MVD

Posted by [Stefano Spataro](#) on Fri, 12 Feb 2010 19:10:58 GMT

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Dear all,

Laura has fixed the calculation of the reconstructed dE/dx in PndPidCorrelator class. You can try to run macro/pid macros and to plot the dE/dx from PidCandidate.

If I shoot the detector with 1GeV/c muons, I have the following dE/dx distribution:

(unity: GeV/cm).

Just fitting the distribution with a landau (as it should be), we obtain the following values:

MPV: 2.83 MeV/cm

sig: 0.23 MeV/cm

If we consider the silicon density $\rho = 2.33 \text{ g/cm}^3$

-> dE/dx ~ 1.21 [MeV cm² / g]

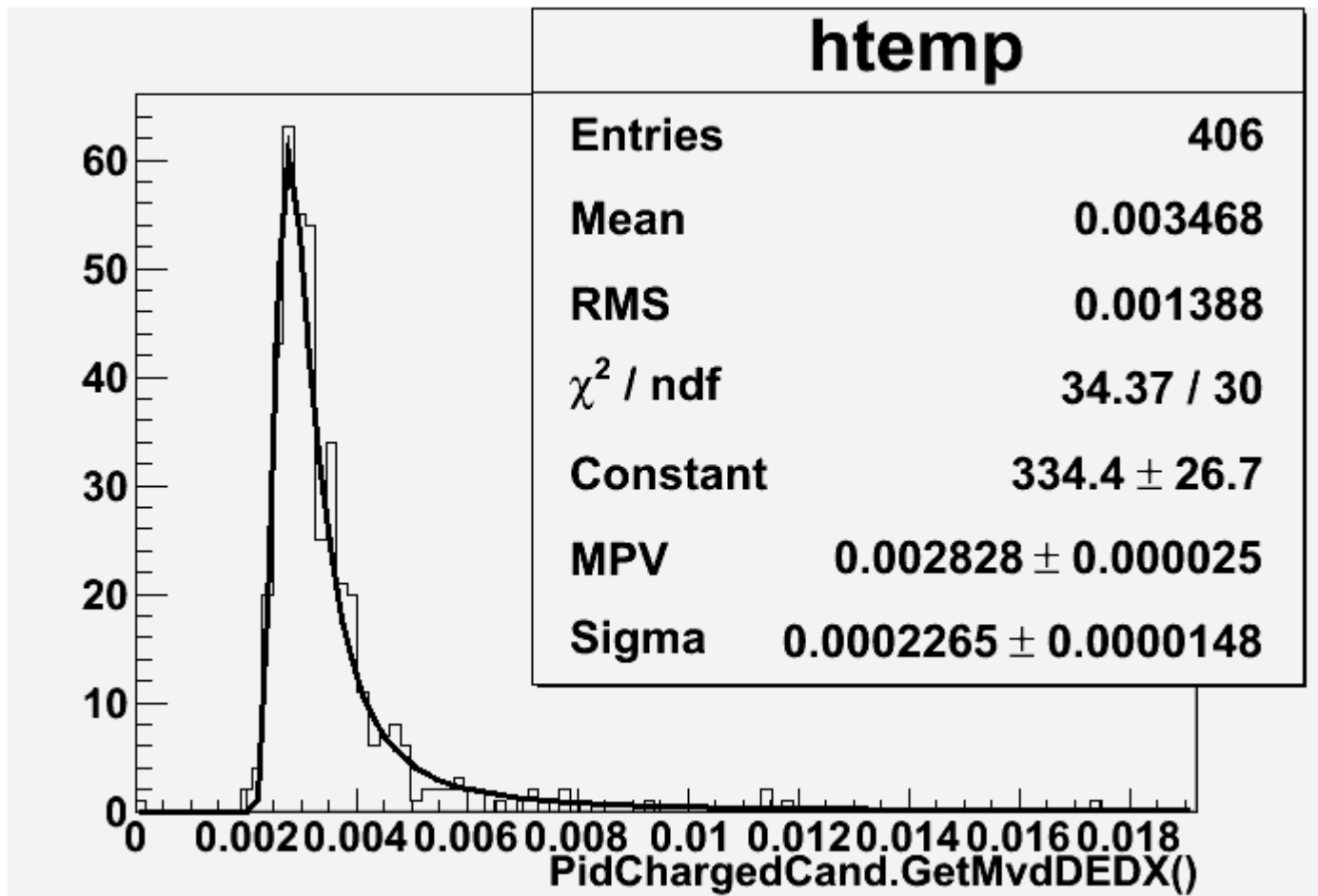
I would like to ask to MVD experts how much is the "theoretical value", I would suppose you have already some tables with the correct values.

We have also compared the reconstructed dE/dx with the MonteCarlo value, and the results seem in agreement, but I would like to know what is coming from "physics" before believing blindly in simulation.

Thanks in advance.

File Attachments

1) [mvd_dedx.gif](#), downloaded 784 times



Subject: Re: Energy loss in MVD
 Posted by [Ralf Kliemt](#) on Thu, 18 Feb 2010 14:19:52 GMT
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Hi Laura, hi Stefano.

I found in the PDG book 2008 (p. 300f) on silicon semiconductor detectors a typical example: At room temperature you produce a electron per 3.67eV energyloss. For a minimum-ionizing particle in 300um silicon this is about 22000 electrons as most probable value. With your MPV I get 23100 electrons in such 300um Si. This is compatible.

In the same book on p. 270 there is a plot for dE/dx for muons in silicon. I use the dashed line for the Landau/Vavilov/Bichsel description at the thickness of 320um and find it close to 1.2 MeVcm²/g for 1GeV muons. This is compatible, too.

Kind regards, Ralf.